CD74HC540, CD74HCT540, CD74HC541, CD74HCT541

High Speed CMOS Logic Octal Buffer and Line Drivers, Three-State

Data sheet acquired from Harris Semiconductor
SCHS189

January 1998

Features

- **CD74HC540, CD74HCT540 . . . . . Inverting**
- **CD74HC541, CD74HCT541 . . . . . .Non-Inverting**
- **Buffered Inputs**
- **Three-State Outputs**
- **Bus Line Driving Capability**
- **Typical Propagation Delay = 9ns at V_{CC} = 5V, C_L = 15pF, T_A = 25^oC**
- **Fanout (Over Temperature Range)**
  - **Standard Outputs . . . . . 10 LSTTL Loads**
  - **Bus Driver Outputs . . . . . 15 LSTTL Loads**
- **Wide Operating Temperature Range . . . -55^oC to 125^oC**
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HC Types**
  - **2V to 6V Operation**
  - **High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V**
- **HCT Types**
  - **4.5V to 5.5V Operation**
  - **Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)**
  - **CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}**

Description

The Harris CD74HC540 and CD74HCT540 are Inverting Octal Buffers and Line Drivers with Three-State Outputs and the capability to drive 15 LSTTL loads. The Harris CD74HC541 and CD74HCT541 are Non-Inverting Octal Buffers and Line Drivers with Three-State Outputs that can drive 15 LSTTL loads. The Output Enables ($\overline{OE1}$) and ($\overline{OE2}$) control the Three-State Outputs. If either $\overline{OE1}$ or $\overline{OE2}$ is HIGH the outputs will be in the high impedance state. For data output $\overline{OE1}$ and $\overline{OE2}$ both must be LOW.

Ordering Information

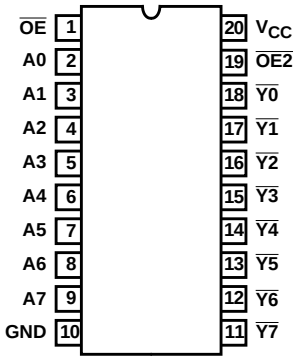
PART NUMBER	TEMP. RANGE (^oC)	PACKAGE	PKG. NO.
CD74HC540E	-55 to 125	20 Ld PDIP	E20.3
CD74HCT540E	-55 to 125	20 Ld PDIP	E20.3
CD74HC541E	-55 to 125	20 Ld PDIP	E20.3
CD74HCT541E	-55 to 125	20 Ld PDIP	E20.3
CD74HC540M	-55 to 125	20 Ld SOIC	M20.3
CD74HCT540M	-55 to 125	20 Ld SOIC	M20.3
CD74HC541M	-55 to 125	20 Ld SOIC	M20.3
CD74HCT541M	-55 to 125	20 Ld SOIC	M20.3

NOTES:

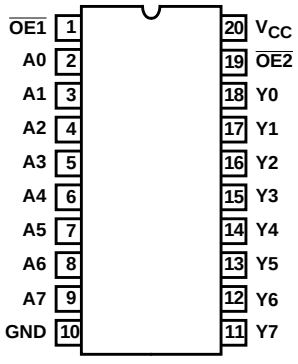
1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer and die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Pinouts

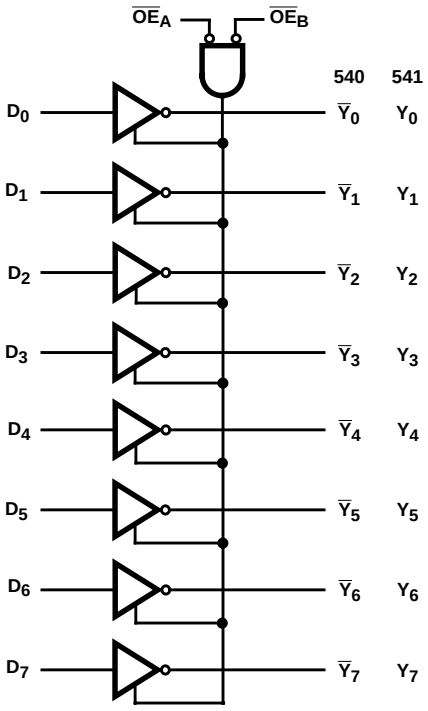
CD74HC540, CD74HCT540
(PDIP, SOIC)
TOP VIEW



CD74HC541, CD74HCT541
(PDIP, SOIC)
TOP VIEW



Functional Diagram



TRUTH TABLE

INPUTS			OUTPUTS	
$\overline{OE1}$	$\overline{OE2}$	An	540	541
L	L	H	L	H
H	X	X	Z	Z
X	H	X	Z	Z
L	L	L	H	L

NOTE:
H = HIGH Voltage Level
L = LOW Voltage Level
X = Don't Care
Z = High Impedance

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
For V_I < -0.5V or V_I > V_{CC} + 0.5V . . . . . ±20mA
DC Output Diode Current, I_{OK}
For V_O < -0.5V or V_O > V_{CC} + 0.5V . . . . . ±20mA
DC Drain Current, per Output, I_O
For -0.5V < V_O < V_{CC} + 0.5V . . . . . ±35mA
DC Output Source or Sink Current per Output Pin, I_O
For V_O > -0.5V or V_O < V_{CC} + 0.5V . . . . . ±25mA
DC V_{CC} or Ground Current, I_{CC} . . . . . ±50mA

Operating Conditions

Temperature Range, T_A . . . . . -55^oC to 125^oC
Supply Voltage Range, V_{CC}
HC Types . . . . . 2V to 6V
HCT Types . . . . . 4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . . 0V to V_{CC}
Input Rise and Fall Time
2V . . . . . 1000ns (Max)
4.5V. . . . . 500ns (Max)
6V . . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 3) θ_{JA} ($^oC/W$)
PDIP Package 125
SOIC Package 120
Maximum Junction Temperature . . . . . 150^oC
Maximum Storage Temperature Range . . . . . -65^oC to 150^oC
Maximum Lead Temperature (Soldering 10s) . . . . . 300^oC
(SOIC - Lead Tips Only)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS V_I (V)	TEST CONDITIONS I_O (mA)	V_{CC} (V)	25°C MIN	25°C TYP	25°C MAX	-40°C TO 85°C MIN	-40°C TO 85°C MAX	-55°C TO 125°C MIN	-55°C TO 125°C MAX	UNITS
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA
Three- State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	V_O = V_{CC} or GND	6	-	-	±0.5	-	±5.0	-	±10	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} and GND	0	5.5	-		±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Three- State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	V_O = V_{CC} or GND	5.5	-	-	±0.5	-	±5.0	-	±10	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI_{CC}	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE: For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS	
	HCT540	HCT541
A0 - A7	1	0.4
$\overline{OE2}$	0.75	0.75
$\overline{OE1}$	1.15	1.15

NOTE: Unit load is ΔI_{CC} limit specific in DC Electrical Specifications Table, e.g., 360µA max. at 25°C.

Switching Specifications C_L = 50pF, Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay Data to Outputs (540)	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	-	110	-	140	-	165	ns
			4.5	-	-	22	-	28	-	33	ns
		C_L = 15pF	5	-	9	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	19	-	24	-	28	ns
Data to Outputs (541)	t_{PLZ}, t_{PHZ}	C_L = 50pF	2	-	-	115	-	145	-	175	ns
			4.5	-	-	23	-	29	-	35	ns
		C_L = 15pF	5	-	9	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	20	-	25	-	30	ns
Output Enable and Disable to Outputs (540)	t_{PLZ}, t_{PHZ}	C_L = 50pF	2	-	-	160	-	200	-	240	ns
			4.5	-	-	32	-	40	-	48	ns
		C_L = 15pF	5	-	13	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	27	-	34	-	41	ns
Output Enable and Disable to Outputs (541)	t_{PLZ}, t_{PHZ}	C_L = 50pF	2	-	-	160	-	200	-	240	ns
			4.5	-	-	32	-	40	-	48	ns
		C_L = 15pF	5	-	14	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	23	-	29	-	35	ns
Output Transition Time	t_{THL}, t_{TLH}	C_L = 50pF	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	C_I	C_L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	C_O	-	-	20	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5) (540)	C_{PD}	C_L = 15pF	5	-	50	-	-	-	-	-	pF
Power Dissipation Capacitance (Notes 4, 5) (541)	C_{PD}	C_L = 15pF	5	-	48	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay Data to Outputs (540)	t_{PHL}, t_{PLH}	C_L = 50pF	4.5	-	-	24	-	30	-	36	ns
		C_L = 15pF	5	-	9	-	-	-	-	-	ns
Data to Outputs (541)	t_{PHL}, t_{PLH}	C_L = 50pF	4.5	-	-	28	-	35	-	42	ns
		C_L = 15pF	5	-	11	-	-	-	-	-	ns
Output Enable and Disable to Outputs (540, 541)	t_{PLZ}, t_{PHZ}	C_L = 50pF	4.5	-	-	35	-	44	-	53	ns
		C_L = 15pF	5	-	14	-	-	-	-	-	ns
Output Transition Time	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	C_I	C_L = 50pF	-	10	-	10	-	10	-	10	pF

Switching Specifications C_L = 50pF, Input t_r, t_f = 6ns **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Three-State Output Capacitance	C_O	-	-	20	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 4, 5) (540, 541)	C_{PD}	C_L = 15pF	5	-	55	-	-	-	-	-	pF

NOTES:

4. C_{PD} is used to determine the dynamic power consumption, per channel.
5. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

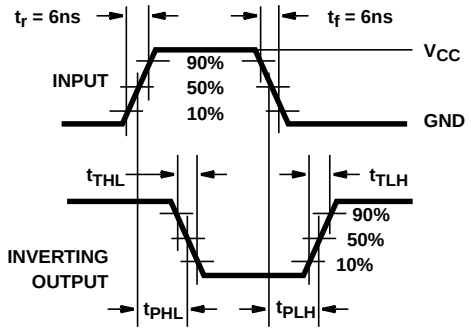


FIGURE 1. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

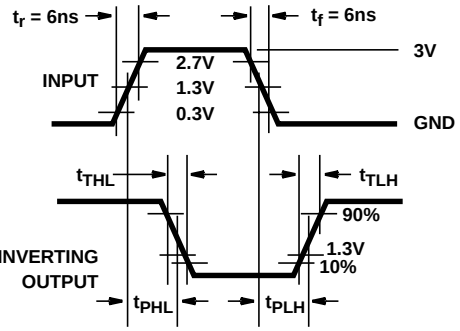


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

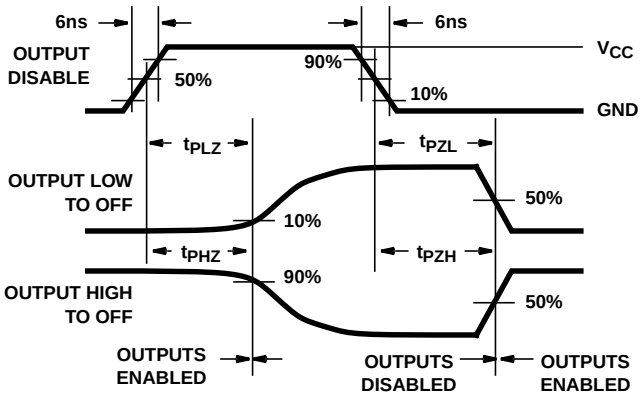


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

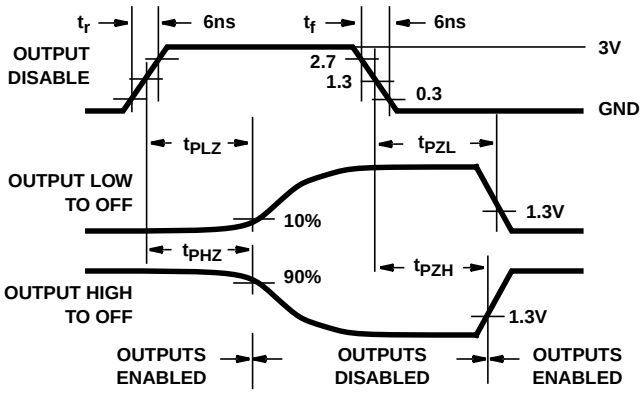
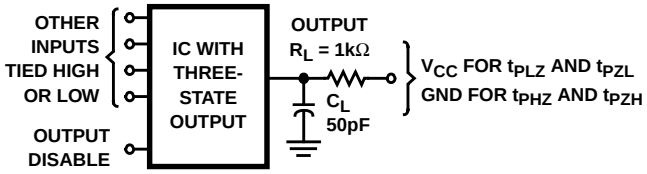


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM

Test Circuits and Waveforms (Continued)



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output R_L = 1kΩ to V_{CC}, C_L = 50pF.

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

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